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EAST - [09917440.wsp:1]						
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	Type	Hit	Search Text		DBs	Time Stamp
Per	43	BRS 1	"4434401" PN		USPAT	2003/06/22
Acti	44	BRS 1	"5032786" PN		USPAT	2003/06/22
Fail	45	BRS 1	"5179433" PN		USPAT	2003/06/22
(46	BRS 1	"5596207" PN		USPAT	2003/06/22
(47	BRS 1	"5548224" PN		USPAT	2003/06/22
(48	BRS 1	"5646074" PN		USPAT	2003/06/22
(49	BRS 1	"5739052" PN		USPAT	2003/06/22
(50	BRS 1	"5759871" PN		USPAT	2003/06/22
(51	BRS 1	"5781445" PN		USPAT	2003/06/22
(52	BRS 1	"5804975" PN		USPAT	2003/06/22
(53	BRS 1	"6028324" PN		USPAT	2003/06/22
(54	BRS 1	"6043102" PN		USPAT	2003/06/22
Save	55	BRS 35	"6028324" "5596207" "5179433" "6040199"		USPAT; US-PGPUB	2003/06/22
(56	BRS 22	"6496959" "5032786" "5804975" "6043102"		USPAT; US-PGPUB	2003/06/22
(57	BRS 1	"4542340" PN		USPAT	2003/06/22
(58	BRS 1	"4588946" PN		USPAT	2003/06/22
(59	BRS 1	"5420520" PN		USPAT	2003/06/22
(60	BRS 1	"5600578" PN		USPAT	2003/06/22
(61	BRS 1	"4382229" PN		USPAT	2003/06/22
(62	BRS 1	"4520448" PN		USPAT	2003/06/22
(63	BRS 1	"4542340" PN		USPAT	2003/06/22
(64	BRS 1	"4789825" PN		USPAT	2003/06/22
(65	BRS 1	"4906921" PN		USPAT	2003/06/22
(66	BRS 1	"5012306" PN		USPAT	2003/06/22
(67	BRS 1	"5093275" PN		USPAT	2003/06/22
(68	BRS 1	"5012306" PN		USPAT	2003/06/22
(69	BRS 1	"5153510" PN		USPAT	2003/06/22
(70	BRS 1	"5381345" PN		USPAT	2003/06/22
(71	BRS 1	"5638006" PN		USPAT	2003/06/22
(72	BRS 1	"5943550" PN		USPAT	2003/06/22
(73	BRS 1	"6043102" PN		USPAT	2003/06/22
(74	BRS 17	"5600578"		USPAT; US-PGPUB	2003/06/22
(75	BRS 4	"5999011"		USPAT; US-PGPUB	2003/06/22
(76	BRS 17	"5600578"		USPAT; US-PGPUB	2003/06/22
(77	BRS 1	"5598009" PN		USPAT; US-PGPUB	2003/06/22
(78	BRS 1	"5625288" PN		USPAT	2003/06/22
(79	BRS 9	"5519336"		USPAT	2003/06/22
(80	BRS 7	"6049213"		USPAT; US-PGPUB	2003/06/22
(81	BRS 0	(substrate with gate with (doped adi ("same conductivity" or "same impurity" or "same doping")) not (sourc		USPAT; US-PGPUB	2003/06/22
(82	BRS 7	"4859938"		USPAT; US-PGPUB	2003/06/22
(83	BRS 1	"3440715" PN		USPAT; US-PGPUB	2003/06/22
(84	BRS 1	"3922707" PN		USPAT	2003/06/22
(85	BRS 1	"3922707" PN		USPAT	2003/06/22

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Per	65 BRS 1	"3943442" PN.	USPAT	2003/06/22	
Acti	66 BRS 1	"4282483" PN.	USPAT	2003/06/22	
Fail	67 BRS 1	"4325025" PN.	USPAT	2003/06/22	
(68 BRS 1	"4567430" PN.	USPAT	2003/06/22	
(68 BRS 1	"4720670" PN.	USPAT	2003/06/22	
(90 BRS 1	"4859938" PN.	USPAT	2003/06/22	
(91 BRS 1	"4894605" PN.	USPAT	2003/06/22	
(92 BRS 1	"4906921" PN.	USPAT	2003/06/22	
(93 BRS 6	"5801538"	USPAT: US-PGPUB	2003/06/22	
(94 BRS 12	((test with capacitor).ab.) and (324/\$3.ccls.) and ((semiconductor or silicon) with substrate)	USPAT: US-PGPUB	2003/06/22	
(95 BRS 12	((complete or full) adj (transistor or fet or mosfet or igfet or misfet or mesfet or (field adj effect))) with ("in	USPAT: US-PGPUB	2003/06/22	
(96 BRS 0	((complete or full) adj (transistor or fet or mosfet or igfet or misfet or mesfet or (field adj effect)) with ("in	USPAT: US-PGPUB	2003/06/22	
(97 BRS 0	((complete or full) adj (transistor or fet or mosfet or igfet or misfet or mesfet or (field adj effect))) with ("in	USPAT: US-PGPUB	2003/06/22	
(98 BRS 19	((gate with "via" with (deposited or formed or sputtered or placed)) and (324/\$3.ccls.)) and ((semiconductor	USPAT: US-PGPUB	2003/06/22	
(99 BRS 26	(gate with "hole" with (deposited or formed or sputtered or placed)) and (324/\$3.ccls.)	USPAT: US-PGPUB	2003/06/22	
(100 BRS 3	((test with capacitor).ti.) and (324/\$3.ccls.) and ((semiconductor or silicon) with substrate)	USPAT: US-PGPUB	2003/06/22	
(101 BRS 4	((stacked adj capacitor)) and (324/\$3.ccls.) and ((semiconductor or silicon) with substrate)	USPAT: US-PGPUB	2003/06/22	
(102 BRS 9	((gate with capacitor).ab.) and (324/\$3.ccls.) and ((semiconductor or silicon) with substrate)	USPAT: US-PGPUB	2003/06/22	
(103 BRS 12	(gate with (contact adj hole)) and (324/\$3.ccls.) and ((semiconductor or silicon) with substrate)	USPAT: US-PGPUB	2003/06/22	
(104 BRS 13	(gate with hole) and (324/769.ccls.) and ((semiconductor or silicon) with substrate)	USPAT: US-PGPUB	2003/06/22	
(105 BRS 0	((complete or full) adj (transistor or fet or mosfet or igfet or misfet or mesfet or (field adj effect)) with ("in	USPAT: US-PGPUB	2003/06/22	
(106 BRS 0	((complete or full) adj (transistor or fet or mosfet or igfet or misfet or mesfet or (field adj effect)) with ("in	USPAT: US-PGPUB	2003/06/22	
(107 BRS 2	((capacitor.ti.)) and (324/769.ccls.)	USPAT: US-PGPUB	2003/06/22	
(108 BRS 8	"5179433"	USPAT: US-PGPUB	2003/06/25	
(109 BRS 2	"5179433"	EPO: JPO: DERWENT: IBM	2003/06/25	
(110 BRS 16	(gate adj depletion adj effect) and (advanced.as.)	USPAT: US-PGPUB	2003/06/25	
(111 BRS 0	(gate adj depletion adj effect) and ((257/48.ccls.))	USPAT: US-PGPUB	2003/06/25	
(112 BRS 1	(gate with (depletion adj effect)) and ((257/48.ccls.))	USPAT: US-PGPUB	2003/06/25	
(113 BRS 1	(gate with (depletion adj effect)) and ((test or testing).ab.)	USPAT: US-PGPUB	2003/06/25	
(114 BRS 0	(((depletion adj effect) and (test or testing)).ab.)	USPAT: US-PGPUB	2003/06/25	
(115 BRS 0	(gate adj depletion) and ((257/48.ccls.))	USPAT: US-PGPUB	2003/06/25	
(116 BRS 0	(((gate adj depletion) and (test or testing)).ab.)	USPAT: US-PGPUB	2003/06/25	
(117 BRS 1	(((gate adj depletion) and ((257/\$3.ccls.) or (438/\$3.ccls.))) and ((test or testing).ab.)	USPAT: US-PGPUB	2003/06/25	
(118 BRS 0	(substrate with gate with (doped adj ("same conductivity" or "same impurity" or "same doping")) not (sourc	USPAT: US-PGPUB	2003/06/25	
(119 BRS 1	"3882391" PN.	USPAT	2003/06/25	
(120 BRS 4	(gate adj depletion) and (324/\$3.ccls.)	USPAT: US-PGPUB	2003/06/25	
(121 BRS 9	("3882391"	USPAT: US-PGPUB	2003/06/25	
(122 BRS 2	(gate adj depletion) and ((test or testing or measure or measuring or measured or tested or determine or d	USPAT: US-PGPUB	2003/06/25	
(123 BRS 1	("3882391"	USPAT: US-PGPUB	2003/06/25	
(124 BRS 1	"6472233"	USPAT: US-PGPUB	2003/06/25	
(125 BRS 2	(((thin adj gate) with depletion) and ((test or testing or measure or measuring or measured or tested or dete	USPAT: US-PGPUB	2003/06/25	
(126 BRS 1	(((thin adj gate) with inversion) and ((test or testing or measure or measuring or measured or tested or dete	USPAT: US-PGPUB	2003/06/25	
(127 BRS 1	"6472233"	USPAT: US-PGPUB	2003/06/25	
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144	BRS	1	"5216362".PN	USPAT	2003/06/25
145	BRS	1	"5485091".PN	USPAT	2003/06/25
146	BRS	1	"5498974".PN	USPAT	2003/06/25
147	BRS	1	"5661408".PN	USPAT	2003/06/25
148	BRS	1	"5773989".PN	USPAT	2003/06/25
149	BRS	1	"5834941".PN	USPAT	2003/06/25
150	BRS	8	(324/\$3.ccls.) and (depletion adi effect)	USPAT; US-PGPUB	2003/06/25
151	BRS	1	(gate with accumulation with depletion) and (257/48.ccls.)	USPAT; US-PGPUB	2003/06/27
152	BRS	5	((test or testing) adi (fet or transistor or mosfet or misfet or igfet or (field adi effect))) with "just"	USPAT; US-PGPUB	2003/06/27
153	BRS	0	((test or testing) adi (fet or transistor or mosfet or misfet or igfet or (field adi effect))) with ((test or testing)	USPAT; US-PGPUB	2003/06/27
154	BRS	4	((test or testing) adi (fet or transistor or mosfet or misfet or igfet or (field adi effect))) with simple	USPAT; US-PGPUB	2003/06/27
155	BRS	1	((test or testing) adi (fet or transistor or mosfet or misfet or igfet or (field adi effect))) and ((capacitor with	USPAT; US-PGPUB	2003/06/27
156	BRS	7	((test or testing) adi (capacitor))) and ((test or testing) adi (fet or transistor or mosfet or misfet or igfet or	USPAT; US-PGPUB	2003/06/27
157	BRS	2	((test or testing) adi capacitor) same ((field adi oxide) or fox or locos or (local adi oxidation)))	USPAT; US-PGPUB	2003/06/27
158	BRS	8	((test or testing) adi (gate or electrode)) same ((field adi oxide) or fox or locos or (local adi oxidation)))	USPAT; US-PGPUB	2003/06/27
159	BRS	7	"6043662"	USPAT; US-PGPUB	2003/06/27
160	BRS	4	((gate or electrode or poly\$1si or poly\$1silicon or (poly adi (si or silicon or crystalline)) or poly\$1crystalline)	USPAT; US-PGPUB	2003/06/27
161	BRS	23	((gate or electrode or poly\$1si or poly\$1silicon or (poly adi (si or silicon or crystalline)) or poly\$1crystalline)	USPAT; US-PGPUB	2003/06/27
162	BRS	20	"5798649"	USPAT; US-PGPUB	2003/06/27
163	BRS	2	((gate or electrode or poly\$1si or poly\$1silicon or (poly adi (si or silicon or crystalline)) or poly\$1crystalline)	USPAT; US-PGPUB	2003/06/27
164	BRS	1	"5049811".PN	USPAT	2003/06/27
165	BRS	1	"5057441".PN	USPAT	2003/06/27
166	BRS	1	"4296372".PN	USPAT	2003/06/27
167	BRS	1	"5049811".PN	USPAT	2003/06/27
168	BRS	1	"5057441".PN	USPAT	2003/06/27
169	BRS	1	"5420513".PN	USPAT	2003/06/27
170	BRS	3	("5798649"	USPAT; US-PGPUB	2003/06/27
171	BRS	1	"4520448".PN	USPAT	2003/06/27
172	BRS	1	"5049811".PN	USPAT	2003/06/27
173	BRS	1	"5057441".PN	USPAT	2003/06/27
174	BRS	1	"5420513".PN	USPAT	2003/06/27
175	BRS	15	"5420513"	USPAT; US-PGPUB	2003/06/27
176	BRS	1	gate with substrate with driven with accumulation	USPAT; US-PGPUB	2003/06/27
177	BRS	1	"4670669".PN	USPAT	2003/06/27
178	BRS	1	"5576565".PN	USPAT	2003/06/27
179	BRS	1	"5608258".PN	USPAT	2003/06/27
180	BRS	1	"5793074".PN	USPAT	2003/06/27
181	BRS	15	capacitor with driven with accumulation	USPAT; US-PGPUB	2003/06/27
182	BRS	34	(capacitor with accumulation) and (324/\$3.cor.)	USPAT; US-PGPUB	2003/06/27
183	BRS	0	(capacitor with accumulation) and (257/48.ccls.)	USPAT; US-PGPUB	2003/06/27
184	BRS	2	(substrate with accumulation) and (257/48.ccls.)	USPAT; US-PGPUB	2003/06/27
185	BRS	36	(capacitor with depletion) and (324/\$3.ccls.)	USPAT; US-PGPUB	2003/06/27
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